Amendment to the Claims

Claims 1-17 (Cancelled)

18. (Currently Amended) A method of mounting a semiconductor laser device comprising:

heating a bonding member to be fused on a submount by heating a table upon which said submount is mounted;

holding a semiconductor laser component with a collet;

contacting portion of said semiconductor laser component.

pressure bonding said semiconductor laser component in a loading position on said submount with said collet so as to mount said semiconductor laser component on said submount; and

terminating the heating operation while the collet pressure bonds the semiconductor laser component to the submount,

wherein the pressure bonding operation is carried out so as to substantially prevent transfer of heat from said semiconductor laser component to said collet. collet, wherein said collet has a contacting side having an area larger than that of a

19.(Previously Presented) The method of mounting a semiconductor laser device according to claim 18, further comprising heating the collet to substantially the same temperature as that of the heating table while the heating table is heated so as to prevent transfer of heat from said semiconductor laser component to said collet.

20.(Previously Presented) The method of mounting a semiconductor laser device according to claim 18, wherein said collet is maintained at a temperature higher than the temperature of said heating table until said bonding member solidifies completely.

21.(Previously Presented) The method of mounting a semiconductor laser device according to claim 18, wherein said semiconductor laser component is heated to substantially the same temperature as the temperature of said collet before said semiconductor laser component is held by said collet.

22.(Previously Presented) The method of mounting a semiconductor laser device according to claim 18, wherein said semiconductor laser component is released from said collet when a part of said bonding member solidifies but prior to complete solidification of the bonding member.

23.(Previously Presented) The method of mounting a semiconductor laser device according to claim 22, wherein said bonding member comprises two or more kinds of materials having different fusing points.

24.(Currently Amended) A method of mounting a semiconductor laser device comprising:

heating a bonding member to be fused on a submount by heating a table upon which said submount is mounted;

holding a semiconductor laser component with a collet;

pressure bonding said semiconductor laser component in a loading position on
said submount with said collet so as to mount said semiconductor laser component on
said submount; and
terminating the heating operation while the collet pressure bonds the
semiconductor laser component to the submount,
wherein the pressure bonding operation is carried out so as to substantially
prevent transfer of heat from said semiconductor laser component to said collet,
wherein said semiconductor laser component is released from said collet when a
part of said bonding member solidifies but prior to complete solidification of the bonding
member, and The method of mounting a semiconductor laser device according to claim
22,
wherein a part of said bonding member is solidified by forced air cooling during
pressure bonding of said semiconductor laser component by said collet.
25.(Previously Presented) The method of mounting a semiconductor laser device
according to claim 18, wherein said bonding member has a fusing point lower than that
of an eutectic solder.
26. (Currently Amended) <u>A method of mounting a semiconductor laser device</u>
comprising:
heating a bonding member to be fused on a submount by heating a table upon
which said submount is mounted;
holding a semiconductor laser component with a collet;

pressure bonding said semiconductor laser component in a loading position on
said submount with said collet so as to mount said semiconductor laser component on
said submount; and
terminating the heating operation while the collet pressure bonds the
semiconductor laser component to the submount,
wherein the pressure bonding operation is carried out so as to substantially
prevent transfer of heat from said semiconductor laser component to said collet, and
The method of mounting a semiconductor laser device according to claim 18,
wherein after said bonding member has solidified, the bonding member is heated
again to a temperature higher than the fusing point.
27. (Cancelled)
28. (Previously Presented) The method of mounting a semiconductor laser device
according to claim 18, wherein said collet has a contacting side face, and a part of said
side face contacts the semiconductor laser component and is made of a material with
low heat conductivity.
29. (Currently Amended) <u>A method of mounting a semiconductor laser device</u>
comprising:
heating a bonding member to be fused on a submount by heating a table upon
which said submount is mounted;
holding a semiconductor laser component with a collet;

pressure bonding said semiconductor laser component in a loading position on
said submount with said collet so as to mount said semiconductor laser component on
said submount; and
terminating the heating operation while the collet pressure bonds the
semiconductor laser component to the submount.
wherein the pressure bonding operation is carried out so as to substantially
prevent transfer of heat from said semiconductor laser component to said collet, and
The method of mounting a semiconductor laser device according to claim 18,
wherein said semiconductor component is bonded near a macro-axis side
thereof on said submount by said bonding member and the remaining parts contact said
submount through a heat transmission member.
30. (Currently Amended) A method of mounting a semiconductor laser device
comprising:
heating a bonding member to be fused on a submount by heating a table upon
which said submount is mounted;
holding a semiconductor laser component with a collet; and
pressure bonding said semiconductor laser component in a loading position on
said submount with said collet so as to mount said semiconductor laser component on
said submount; and
releasing said semiconductor laser component from said collet upon solidification
of only a part of said bonding member <u>, and</u>
wherein said collet has a contacting side having an area larger than that of a

contacting portion of said semiconductor laser component.

31.(Previously Presented) The method of mounting a semiconductor laser device according to claim 30, wherein said bonding member comprises two or more kinds of materials having different fusing points.

33. (Currently Amended) A method of mounting a semiconductor laser device comprising:

heating a bonding member to be fused on a submount by heating a table on

which said submount is mounted;

holding a semiconductor laser component with a collet; and

pressure bonding said semiconductor laser component in a loading position on said submount with said collet so as to mount said semiconductor laser component on said submount,

wherein said bonding member has a fusing point that is lower than that of an eutectic solder, and

wherein said collet has a contacting side having an area larger than that of a contacting portion of said semiconductor laser component.

34. (Previously Presented) The method of mounting a semiconductor laser device according to claim 19, wherein the heating of the table and the collet are simultaneously terminated.